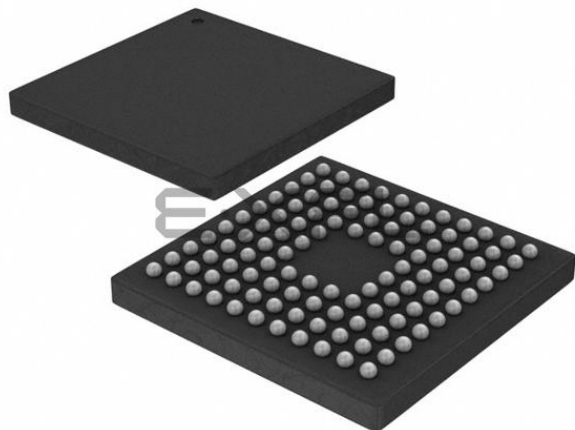




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"[Embedded - Microcontrollers](#)" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "[Embedded - Microcontrollers](#)"

Details

Product Status	Active
Core Processor	ARM® Cortex®-M3
Core Size	32-Bit Single-Core
Speed	48MHz
Connectivity	EBI/EMI, I ² C, IrDA, SmartCard, SPI, UART/USART
Peripherals	Brown-out Detect/Reset, DMA, POR, PWM, WDT
Number of I/O	90
Program Memory Size	1MB (1M x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	128K x 8
Voltage - Supply (Vcc/Vdd)	1.98V ~ 3.8V
Data Converters	A/D 8x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	112-LFBGA
Supplier Device Package	112-BGA (10x10)
Purchase URL	https://www.e-xfl.com/product-detail/silicon-labs/efm32gg290f1024g-e-bga112r

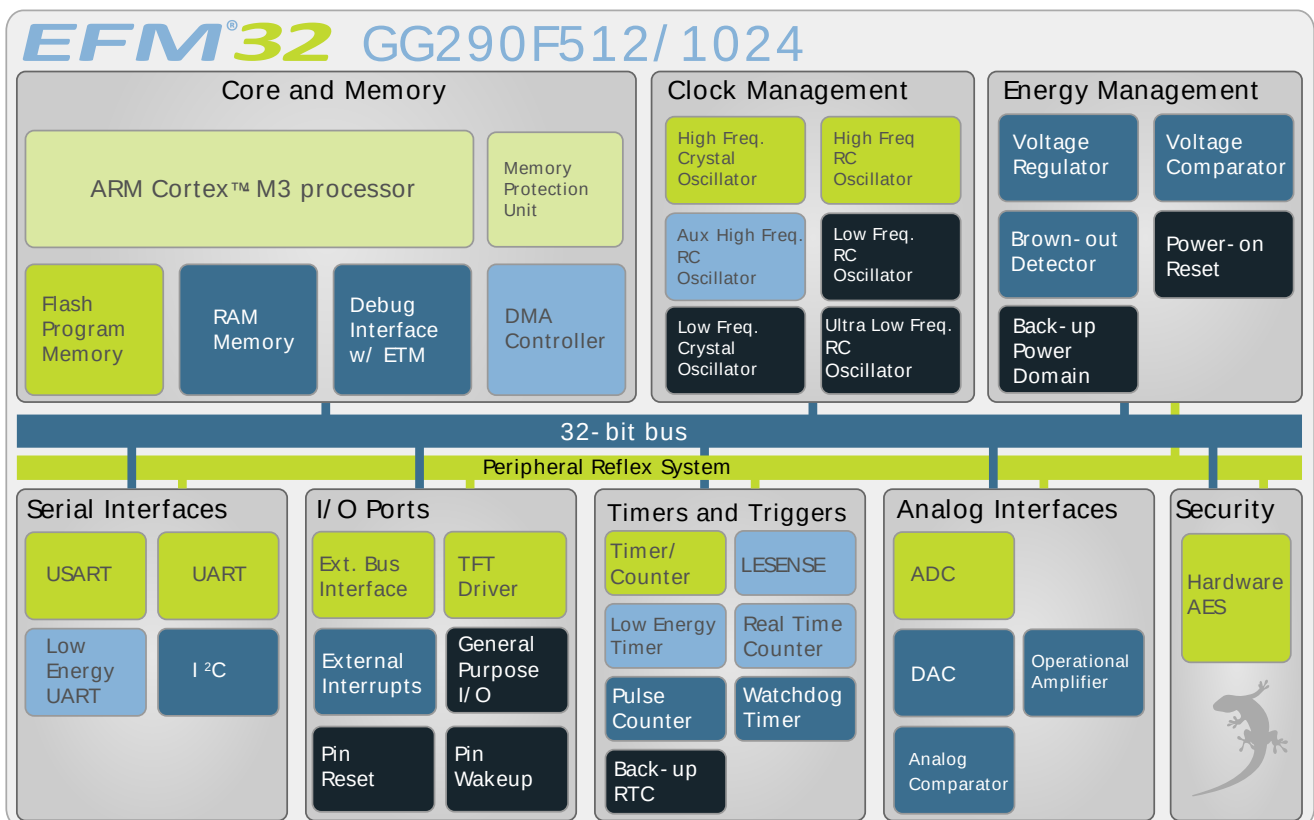
2 System Summary

2.1 System Introduction

The EFM32 MCUs are the world's most energy friendly microcontrollers. With a unique combination of the powerful 32-bit ARM Cortex-M3, innovative low energy techniques, short wake-up time from energy saving modes, and a wide selection of peripherals, the EFM32GG microcontroller is well suited for any battery operated application as well as other systems requiring high performance and low-energy consumption. This section gives a short introduction to each of the modules in general terms and also shows a summary of the configuration for the EFM32GG290 devices. For a complete feature set and in-depth information on the modules, the reader is referred to the *EFM32GG Reference Manual*.

A block diagram of the EFM32GG290 is shown in Figure 2.1 (p. 3) .

Figure 2.1. Block Diagram



2.1.1 ARM Cortex-M3 Core

The ARM Cortex-M3 includes a 32-bit RISC processor which can achieve as much as 1.25 Dhrystone MIPS/MHz. A Memory Protection Unit with support for up to 8 memory segments is included, as well as a Wake-up Interrupt Controller handling interrupts triggered while the CPU is asleep. The EFM32 implementation of the Cortex-M3 is described in detail in *EFM32 Cortex-M3 Reference Manual*.

2.1.2 Debug Interface (DBG)

This device includes hardware debug support through a 2-pin serial-wire debug interface and an Embedded Trace Module (ETM) for data/instruction tracing. In addition there is also a 1-wire Serial Wire Viewer pin which can be used to output profiling information, data trace and software-generated messages.

2.1.3 Memory System Controller (MSC)

The Memory System Controller (MSC) is the program memory unit of the EFM32GG microcontroller. The flash memory is readable and writable from both the Cortex-M3 and DMA. The flash memory is divided into two blocks; the main block and the information block. Program code is normally written to the main block. Additionally, the information block is available for special user data and flash lock bits. There is also a read-only page in the information block containing system and device calibration data. Read and write operations are supported in the energy modes EM0 and EM1.

2.1.4 Direct Memory Access Controller (DMA)

The Direct Memory Access (DMA) controller performs memory operations independently of the CPU. This has the benefit of reducing the energy consumption and the workload of the CPU, and enables the system to stay in low energy modes when moving for instance data from the USART to RAM or from the External Bus Interface to a PWM-generating timer. The DMA controller uses the PL230 μ DMA controller licensed from ARM.

2.1.5 Reset Management Unit (RMU)

The RMU is responsible for handling the reset functionality of the EFM32GG.

2.1.6 Energy Management Unit (EMU)

The Energy Management Unit (EMU) manage all the low energy modes (EM) in EFM32GG microcontrollers. Each energy mode manages if the CPU and the various peripherals are available. The EMU can also be used to turn off the power to unused SRAM blocks.

2.1.7 Clock Management Unit (CMU)

The Clock Management Unit (CMU) is responsible for controlling the oscillators and clocks on-board the EFM32GG. The CMU provides the capability to turn on and off the clock on an individual basis to all peripheral modules in addition to enable/disable and configure the available oscillators. The high degree of flexibility enables software to minimize energy consumption in any specific application by not wasting power on peripherals and oscillators that are inactive.

2.1.8 Watchdog (WDOG)

The purpose of the watchdog timer is to generate a reset in case of a system failure, to increase application reliability. The failure may e.g. be caused by an external event, such as an ESD pulse, or by a software failure.

2.1.9 Peripheral Reflex System (PRS)

The Peripheral Reflex System (PRS) system is a network which lets the different peripheral module communicate directly with each other without involving the CPU. Peripheral modules which send out Reflex signals are called producers. The PRS routes these reflex signals to consumer peripherals which apply actions depending on the data received. The format for the Reflex signals is not given, but edge triggers and other functionality can be applied by the PRS.

2.1.10 External Bus Interface (EBI)

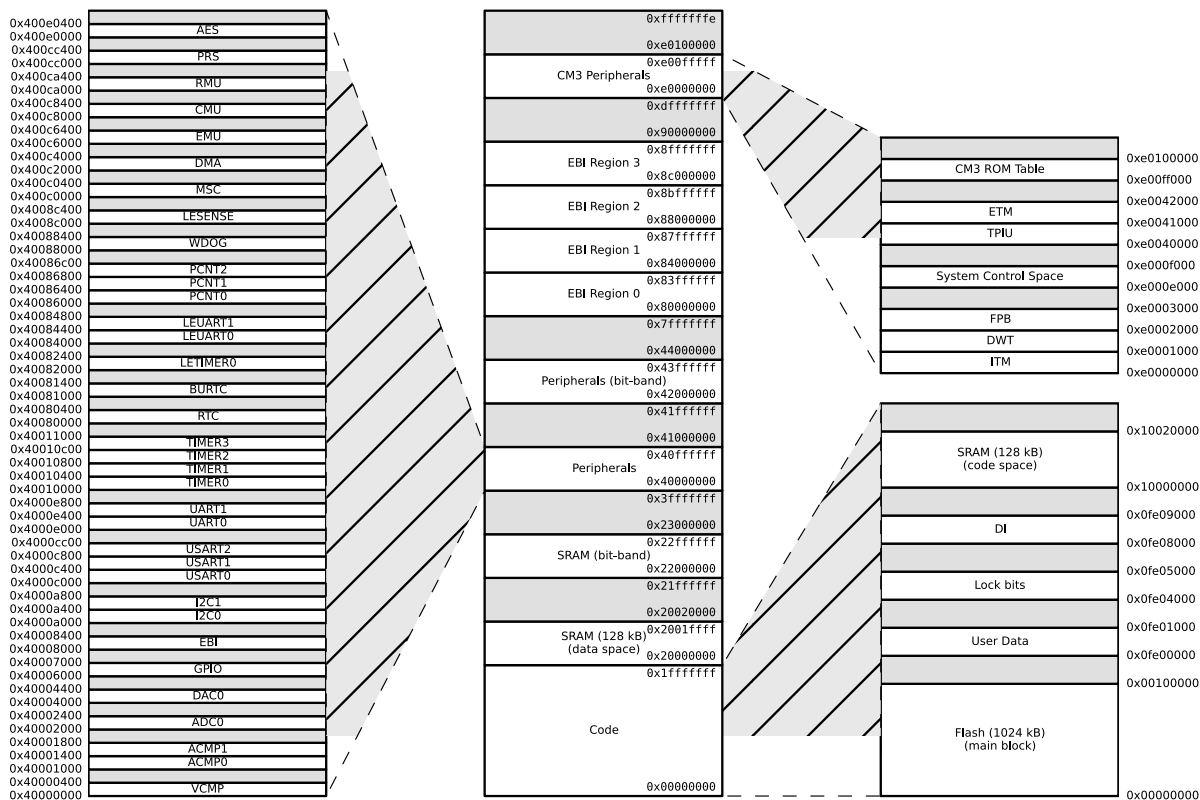
The External Bus Interface provides access to external parallel interface devices such as SRAM, FLASH, ADCs and LCDs. The interface is memory mapped into the address bus of the Cortex-M3. This enables seamless access from software without manually manipulating the IO settings each time a read or write is performed. The data and address lines are multiplexed in order to reduce the number of pins required to interface the external devices. The timing is adjustable to meet specifications of the external devices. The interface is limited to asynchronous devices.

Module	Configuration	Pin Connections
PRS	Full configuration	NA
EBI	Full configuration	EBI_A[27:0], EBI_AD[15:0], EBI_ARDY, EBI_ALE, EBI_BL[1:0], EBI_CS[3:0], EBI_CSTFT, EBI_DCLK, EBI_DTEN, EBI_HSNc, EBI_NANDREn, EBI_NANDWEn, EBI_REn, EBI_VSNc, EBI_WEn
I2C0	Full configuration	I2C0_SDA, I2C0_SCL
I2C1	Full configuration	I2C1_SDA, I2C1_SCL
USART0	Full configuration with IrDA	US0_TX, US0_RX, US0_CLK, US0_CS
USART1	Full configuration with I2S	US1_TX, US1_RX, US1_CLK, US1_CS
USART2	Full configuration with I2S	US2_TX, US2_RX, US2_CLK, US2_CS
UART0	Full configuration	U0_TX, U0_RX
UART1	Full configuration	U1_TX, U1_RX
LEUART0	Full configuration	LEU0_TX, LEU0_RX
LEUART1	Full configuration	LEU1_TX, LEU1_RX
TIMER0	Full configuration with DTI	TIM0_CC[2:0], TIM0_CDTI[2:0]
TIMER1	Full configuration	TIM1_CC[2:0]
TIMER2	Full configuration	TIM2_CC[2:0]
TIMER3	Full configuration	TIM3_CC[2:0]
RTC	Full configuration	NA
BURTC	Full configuration	NA
LETIMER0	Full configuration	LET0_O[1:0]
PCNT0	Full configuration, 16-bit count register	PCNT0_S[1:0]
PCNT1	Full configuration, 8-bit count register	PCNT1_S[1:0]
PCNT2	Full configuration, 8-bit count register	PCNT2_S[1:0]
ACMP0	Full configuration	ACMP0_CH[7:0], ACMP0_O
ACMP1	Full configuration	ACMP1_CH[7:0], ACMP1_O
VCMP	Full configuration	NA
ADC0	Full configuration	ADC0_CH[7:0]
DAC0	Full configuration	DAC0_OUT[1:0], DAC0_OUTxALT
OPAMP	Full configuration	Outputs: OPAMP_OUTx, OPAMP_OUTxALT, Inputs: OPAMP_Px, OPAMP_Nx
AES	Full configuration	NA
GPIO	90 pins	Available pins are shown in Table 4.3 (p. 63)

2.3 Memory Map

The *EFM32GG290* memory map is shown in Figure 2.2 (p. 9), with RAM and Flash sizes for the largest memory configuration.

Figure 2.2. EFM32GG290 Memory Map with largest RAM and Flash sizes



3 Electrical Characteristics

3.1 Test Conditions

3.1.1 Typical Values

The typical data are based on $T_{AMB}=25^{\circ}\text{C}$ and $V_{DD}=3.0\text{ V}$, as defined in Table 3.2 (p. 10), unless otherwise specified.

3.1.2 Minimum and Maximum Values

The minimum and maximum values represent the worst conditions of ambient temperature, supply voltage and frequencies, as defined in Table 3.2 (p. 10), unless otherwise specified.

3.2 Absolute Maximum Ratings

The absolute maximum ratings are stress ratings, and functional operation under such conditions are not guaranteed. Stress beyond the limits specified in Table 3.1 (p. 10) may affect the device reliability or cause permanent damage to the device. Functional operating conditions are given in Table 3.2 (p. 10).

Table 3.1. Absolute Maximum Ratings

Symbol	Parameter	Condition	Min	Typ	Max	Unit
T_{STG}	Storage temperature range		-40		150	$^{\circ}\text{C}$
T_S	Maximum soldering temperature	Latest IPC/JEDEC J-STD-020 Standard			260	$^{\circ}\text{C}$
V_{DDMAX}	External main supply voltage		0		3.8	V
V_{IOPIN}	Voltage on any I/O pin		-0.3		$V_{DD}+0.3$	V
I_{IOMAX}	Current per I/O pin (sink)				100	mA
	Current per I/O pin (source)				-100	mA

3.3 General Operating Conditions

3.3.1 General Operating Conditions

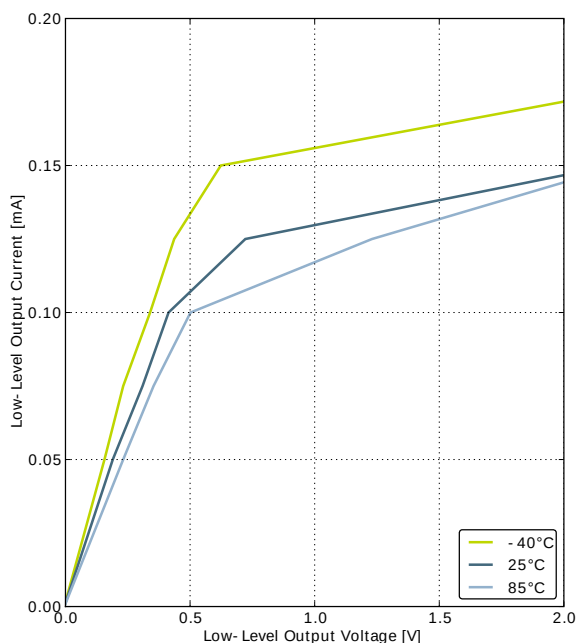
Table 3.2. General Operating Conditions

Symbol	Parameter	Min	Typ	Max	Unit
T_{AMB}	Ambient temperature range	-40		85	$^{\circ}\text{C}$
V_{DDOP}	Operating supply voltage	1.98		3.8	V
f_{APB}	Internal APB clock frequency			48	MHz
f_{AHB}	Internal AHB clock frequency			48	MHz

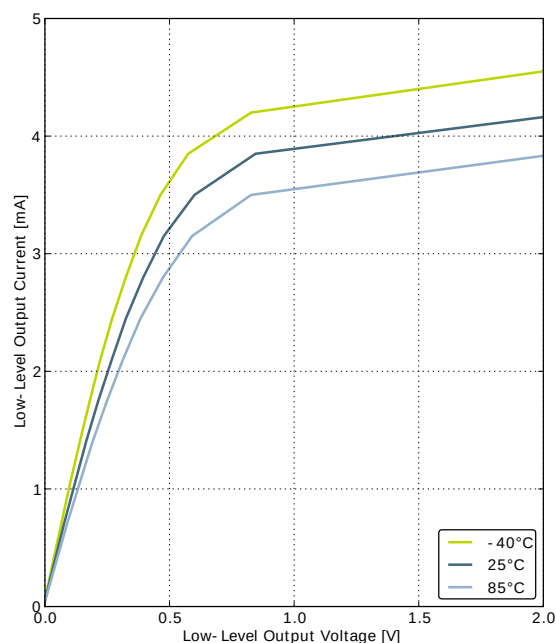
3.8 General Purpose Input Output

Table 3.7. GPIO

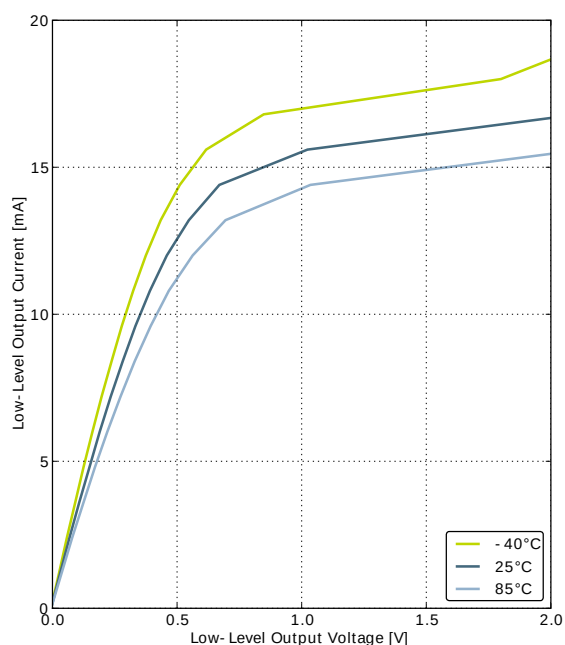
Symbol	Parameter	Condition	Min	Typ	Max	Unit
V _{IOIL}	Input low voltage				0.30V _{DD}	V
V _{IOIH}	Input high voltage		0.70V _{DD}			V
V _{IOOH}	Output high voltage (Production test condition = 3.0V, DRIVEMODE = STANDARD)	Sourcing 0.1 mA, V _{DD} =1.98 V, GPIO_Px_CTRL DRIVEMODE = LOWEST		0.80V _{DD}		V
		Sourcing 0.1 mA, V _{DD} =3.0 V, GPIO_Px_CTRL DRIVEMODE = LOWEST		0.90V _{DD}		V
		Sourcing 1 mA, V _{DD} =1.98 V, GPIO_Px_CTRL DRIVEMODE = LOW		0.85V _{DD}		V
		Sourcing 1 mA, V _{DD} =3.0 V, GPIO_Px_CTRL DRIVEMODE = LOW		0.90V _{DD}		V
		Sourcing 6 mA, V _{DD} =1.98 V, GPIO_Px_CTRL DRIVEMODE = STANDARD	0.75V _{DD}			V
		Sourcing 6 mA, V _{DD} =3.0 V, GPIO_Px_CTRL DRIVEMODE = STANDARD	0.85V _{DD}			V
		Sourcing 20 mA, V _{DD} =1.98 V, GPIO_Px_CTRL DRIVEMODE = HIGH	0.60V _{DD}			V
		Sourcing 20 mA, V _{DD} =3.0 V, GPIO_Px_CTRL DRIVEMODE = HIGH	0.80V _{DD}			V
V _{IOOL}	Output low voltage (Production test condition = 3.0V, DRIVEMODE = STANDARD)	Sinking 0.1 mA, V _{DD} =1.98 V, GPIO_Px_CTRL DRIVEMODE = LOWEST		0.20V _{DD}		V
		Sinking 0.1 mA, V _{DD} =3.0 V, GPIO_Px_CTRL DRIVEMODE = LOWEST		0.10V _{DD}		V
		Sinking 1 mA, V _{DD} =1.98 V, GPIO_Px_CTRL DRIVEMODE = LOW		0.10V _{DD}		V
		Sinking 1 mA, V _{DD} =3.0 V, GPIO_Px_CTRL DRIVEMODE = LOW		0.05V _{DD}		V
		Sinking 6 mA, V _{DD} =1.98 V, GPIO_Px_CTRL DRIVEMODE = STANDARD			0.30V _{DD}	V
		Sinking 6 mA, V _{DD} =3.0 V, GPIO_Px_CTRL DRIVEMODE = STANDARD			0.20V _{DD}	V
		Sinking 20 mA, V _{DD} =1.98 V, GPIO_Px_CTRL DRIVEMODE = HIGH			0.35V _{DD}	V

Figure 3.4. Typical Low-Level Output Current, 2V Supply Voltage

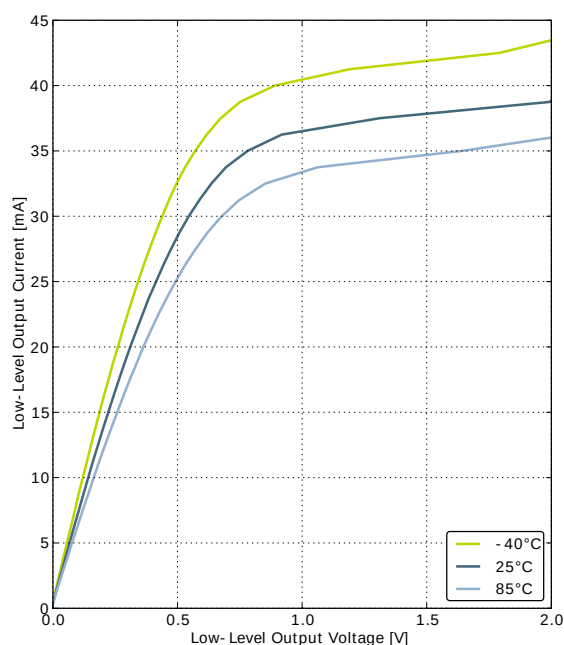
GPIO_Px_CTRL DRIVEMODE = LOWEST



GPIO_Px_CTRL DRIVEMODE = LOW



GPIO_Px_CTRL DRIVEMODE = STANDARD



GPIO_Px_CTRL DRIVEMODE = HIGH

3.9 Oscillators

3.9.1 LFXO

Table 3.8. LFXO

Symbol	Parameter	Condition	Min	Typ	Max	Unit
f_{LFXO}	Supported nominal crystal frequency			32.768		kHz
ESR_{LFXO}	Supported crystal equivalent series resistance (ESR)			30	120	kOhm
C_{LFXOL}	Supported crystal external load range		$\times^1$		25	pF
DC_{LFXO}	Duty cycle		48	50	53.5	%
I_{LFXO}	Current consumption for core and buffer after startup.	ESR=30 kOhm, $C_L=10$ pF, LFXOBOOST in CMU_CTRL is 1		190		nA
t_{LFXO}	Start- up time.	ESR=30 kOhm, $C_L=10$ pF, 40% - 60% duty cycle has been reached, LFXOBOOST in CMU_CTRL is 1		400		ms

¹See Minimum Load Capacitance (C_{LFXOL}) Requirement For Safe Crystal Startup in energyAware Designer in Simplicity Studio

For safe startup of a given crystal, the Configurator tool in Simplicity Studio contains a tool to help users configure both load capacitance and software settings for using the LFXO. For details regarding the crystal configuration, the reader is referred to application note "AN0016 EFM32 Oscillator Design Consideration".

3.9.2 HFXO

Table 3.9. HFXO

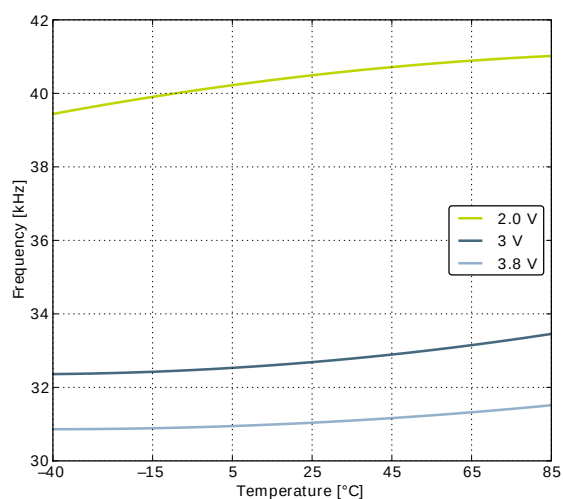
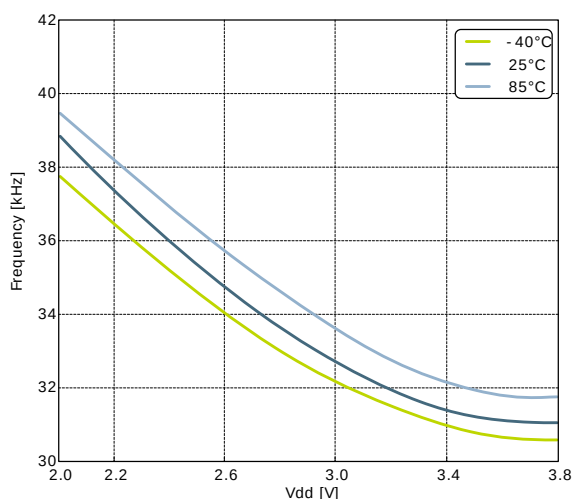
Symbol	Parameter	Condition	Min	Typ	Max	Unit
f_{HFXO}	Supported nominal crystal Frequency		4		48	MHz
ESR_{HFXO}	Supported crystal equivalent series resistance (ESR)	Crystal frequency 48 MHz			50	Ohm
		Crystal frequency 32 MHz		30	60	Ohm
		Crystal frequency 4 MHz		400	1500	Ohm
g_{mHFXO}	The transconductance of the HFXO input transistor at crystal startup	HFXOBOOST in CMU_CTRL equals 0b11	20			mS
C_{HFXOL}	Supported crystal external load range		5		25	pF
I_{HFXO}	Current consumption for HFXO after startup	4 MHz: ESR=400 Ohm, $C_L=20$ pF, HFXOBOOST in CMU_CTRL equals 0b11		85		μ A
		32 MHz: ESR=30 Ohm, $C_L=10$ pF, HFXOBOOST in CMU_CTRL equals 0b11		165		μ A
t_{HFXO}	Startup time	32 MHz: ESR=30 Ohm, $C_L=10$ pF, HFXOBOOST in CMU_CTRL equals 0b11		400		μ s

3.9.3 LFRCO

Table 3.10. LFRCO

Symbol	Parameter	Condition	Min	Typ	Max	Unit
f_{LFRCO}	Oscillation frequency, $V_{\text{DD}} = 3.0 \text{ V}$, $T_{\text{AMB}} = 25^\circ\text{C}$		31.29	32.768	34.28	kHz
t_{LFRCO}	Startup time not including software calibration			150		μs
I_{LFRCO}	Current consumption			300	900	nA
$\text{TUNESTEP}_{\text{LFRCO}}$	Frequency step for LSB change in TUNING value			1.5		%

Figure 3.10. Calibrated LFRCO Frequency vs Temperature and Supply Voltage



3.9.4 HFRCO

Table 3.11. HFRCO

Symbol	Parameter	Condition	Min	Typ	Max	Unit
f_{HFRCO}	Oscillation frequency, $V_{\text{DD}} = 3.0 \text{ V}$, $T_{\text{AMB}} = 25^\circ\text{C}$	28 MHz frequency band	27.5	28.0	28.5	MHz
		21 MHz frequency band	20.6	21.0	21.4	MHz
		14 MHz frequency band	13.7	14.0	14.3	MHz
		11 MHz frequency band	10.8	11.0	11.2	MHz
		7 MHz frequency band	6.48 ¹	6.60 ¹	6.72 ¹	MHz
		1 MHz frequency band	1.15 ²	1.20 ²	1.25 ²	MHz
$t_{\text{HFRCO_settling}}$	Settling time after start-up	$f_{\text{HFRCO}} = 14 \text{ MHz}$		0.6		Cycles
	Settling time after band switch			25		Cycles

Symbol	Parameter	Condition	Min	Typ	Max	Unit
C _{ADCIN}	Input capacitance			2		pF
R _{ADCIN}	Input ON resistance		1			MOhm
R _{ADCFILT}	Input RC filter resistance			10		kOhm
C _{ADCFILT}	Input RC filter/de-coupling capacitance			250		fF
f _{ADCCLK}	ADC Clock Frequency				13	MHz
t _{ADCCONV}	Conversion time	6 bit	7			ADC-CLK Cycles
		8 bit	11			ADC-CLK Cycles
		12 bit	13			ADC-CLK Cycles
t _{ADCACQ}	Acquisition time	Programmable	1		256	ADC-CLK Cycles
t _{ADCACQVDD3}	Required acquisition time for VDD/3 reference		2			μs
t _{ADCSTART}	Startup time of reference generator and ADC core in NORMAL mode			5		μs
	Startup time of reference generator and ADC core in KEEPADCWARM mode			1		μs
SNR _{ADC}	Signal to Noise Ratio (SNR)	1 MSamples/s, 12 bit, single ended, internal 1.25V reference		59		dB
		1 MSamples/s, 12 bit, single ended, internal 2.5V reference		63		dB
		1 MSamples/s, 12 bit, single ended, V _{DD} reference		65		dB
		1 MSamples/s, 12 bit, differential, internal 1.25V reference		60		dB
		1 MSamples/s, 12 bit, differential, internal 2.5V reference		65		dB
		1 MSamples/s, 12 bit, differential, 5V reference		54		dB
		1 MSamples/s, 12 bit, differential, V _{DD} reference		67		dB
		1 MSamples/s, 12 bit, differential, 2xV _{DD} reference		69		dB

Symbol	Parameter	Condition	Min	Typ	Max	Unit
		200 kSamples/s, 12 bit, differential, $2 \times V_{DD}$ reference		69		dB
SFDR _{ADC}	Spurious-Free Dynamic Range (SFDR)	1 MSamples/s, 12 bit, single ended, internal 1.25V reference		64		dBc
		1 MSamples/s, 12 bit, single ended, internal 2.5V reference		76		dBc
		1 MSamples/s, 12 bit, single ended, V_{DD} reference		73		dBc
		1 MSamples/s, 12 bit, differential, internal 1.25V reference		66		dBc
		1 MSamples/s, 12 bit, differential, internal 2.5V reference		77		dBc
		1 MSamples/s, 12 bit, differential, V_{DD} reference		76		dBc
		1 MSamples/s, 12 bit, differential, $2 \times V_{DD}$ reference		75		dBc
		1 MSamples/s, 12 bit, differential, 5V reference		69		dBc
		200 kSamples/s, 12 bit, single ended, internal 1.25V reference		75		dBc
		200 kSamples/s, 12 bit, single ended, internal 2.5V reference		75		dBc
		200 kSamples/s, 12 bit, single ended, V_{DD} reference		76		dBc
		200 kSamples/s, 12 bit, differential, internal 1.25V reference		79		dBc
		200 kSamples/s, 12 bit, differential, internal 2.5V reference		79		dBc
		200 kSamples/s, 12 bit, differential, 5V reference		78		dBc
		200 kSamples/s, 12 bit, differential, V_{DD} reference	68	79		dBc
		200 kSamples/s, 12 bit, differential, $2 \times V_{DD}$ reference		79		dBc
V _{ADCOFFSET}	Offset voltage	After calibration, single ended		0.3		mV
		After calibration, differential	-3	0.3	3	mV
TGRAD _{ADCTH}	Thermometer output gradient			-1.92		mV/°C
				-6.3		ADC Codes/°C
DNL _{ADC}	Differential non-linearity (DNL)	$V_{DD} = 3.0$ V, external 2.5V reference	-1	±0.7	4	LSB
INL _{ADC}	Integral non-linearity (INL), End point method			±1.2	±3.0	LSB
MC _{ADC}	No missing codes		11.999 ¹	12		bits

Figure 3.18. Differential Non-Linearity (DNL)

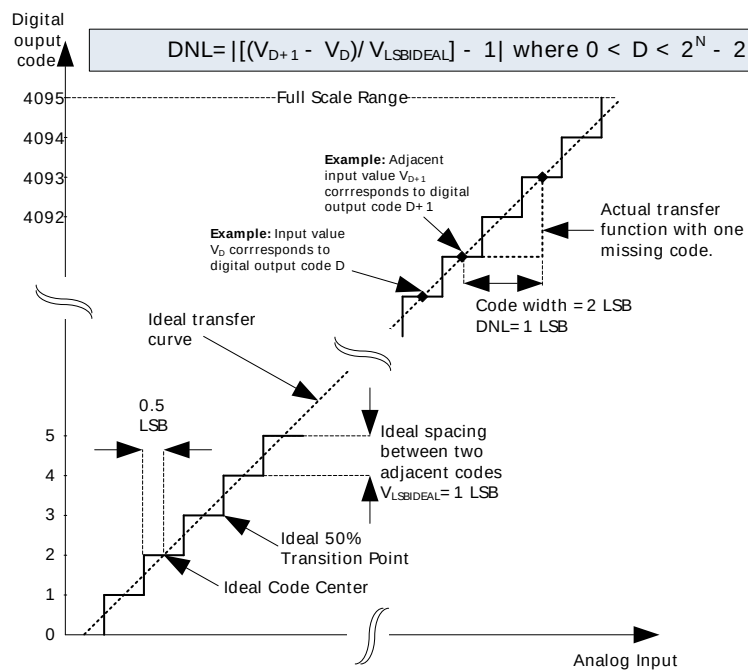
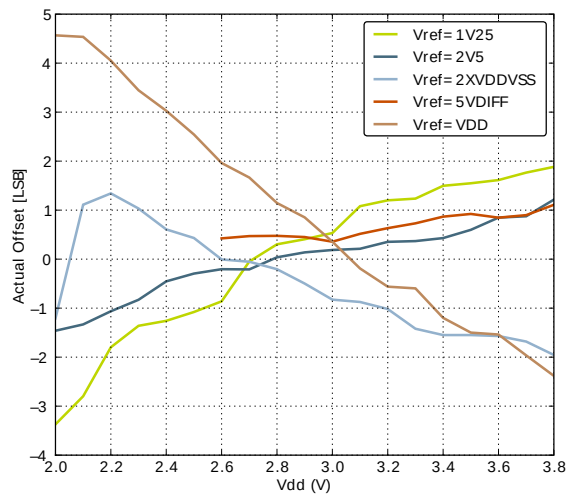
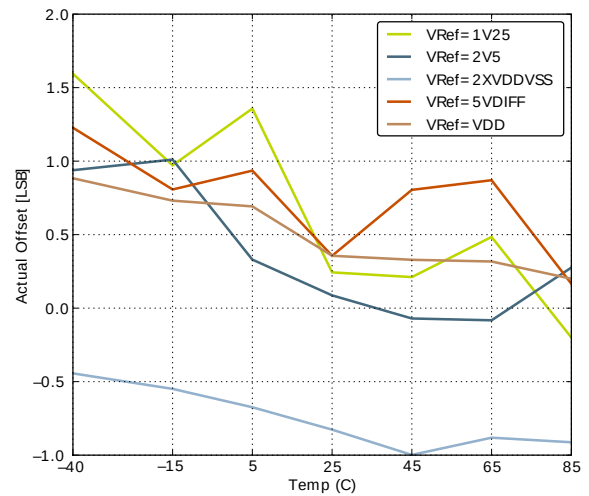


Figure 3.22. ADC Absolute Offset, Common Mode = $V_{dd}/2$

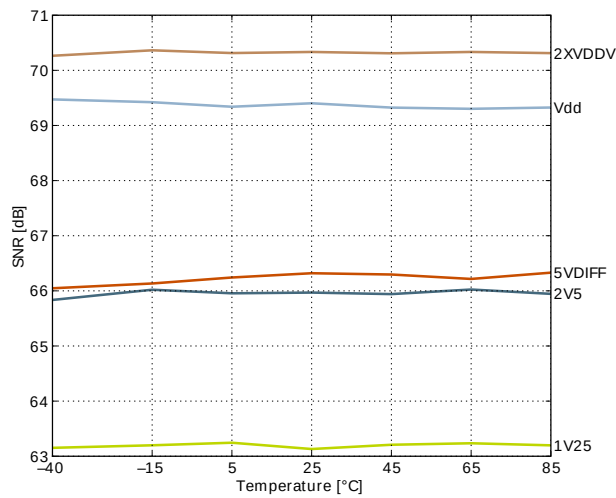


Offset vs Supply Voltage, Temp = 25°C

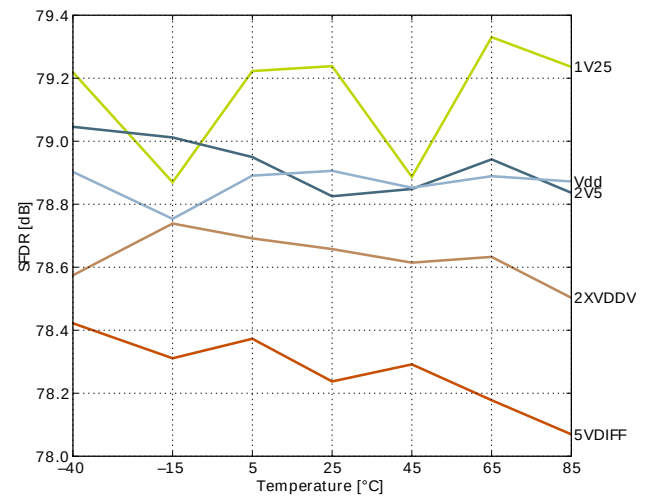


Offset vs Temperature, $V_{dd} = 3V$

Figure 3.23. ADC Dynamic Performance vs Temperature for all ADC References, $V_{dd} = 3V$



Signal to Noise Ratio (SNR)



Spurious-Free Dynamic Range (SFDR)

Symbol	Parameter	Condition	Min	Typ	Max	Unit
		(OPA2)BIASPROG=0x0, (OPA2)HALFBIAS=0x1, Unity Gain		13	17	μA
G _{OL}	Open Loop Gain	(OPA2)BIASPROG=0xF, (OPA2)HALFBIAS=0x0		101		dB
		(OPA2)BIASPROG=0x7, (OPA2)HALFBIAS=0x1		98		dB
		(OPA2)BIASPROG=0x0, (OPA2)HALFBIAS=0x1		91		dB
GBW _{OPAMP}	Gain Bandwidth Product	(OPA2)BIASPROG=0xF, (OPA2)HALFBIAS=0x0		6.1		MHz
		(OPA2)BIASPROG=0x7, (OPA2)HALFBIAS=0x1		1.8		MHz
		(OPA2)BIASPROG=0x0, (OPA2)HALFBIAS=0x1		0.25		MHz
PM _{OPAMP}	Phase Margin	(OPA2)BIASPROG=0xF, (OPA2)HALFBIAS=0x0, C _L =75 pF		64		°
		(OPA2)BIASPROG=0x7, (OPA2)HALFBIAS=0x1, C _L =75 pF		58		°
		(OPA2)BIASPROG=0x0, (OPA2)HALFBIAS=0x1, C _L =75 pF		58		°
R _{INPUT}	Input Resistance			100		Mohm
R _{LOAD}	Load Resistance		200			Ohm
I _{LOAD_DC}	DC Load Current				11	mA
V _{INPUT}	Input Voltage	OPAxHCMDIS=0	V _{SS}		V _{DD}	V
		OPAxHCMDIS=1	V _{SS}		V _{DD} -1.2	V
V _{OUTPUT}	Output Voltage		V _{SS}		V _{DD}	V
V _{OFFSET}	Input Offset Voltage	Unity Gain, V _{SS} <V _{in} <V _{DD} , OPAxHCMDIS=0	-13	0	11	mV
		Unity Gain, V _{SS} <V _{in} <V _{DD} -1.2, OPAxHCMDIS=1		1		mV
V _{OFFSET_DRIFT}	Input Offset Voltage Drift				0.02	mV/°C
SR _{OPAMP}	Slew Rate	(OPA2)BIASPROG=0xF, (OPA2)HALFBIAS=0x0		3.2		V/μs
		(OPA2)BIASPROG=0x7, (OPA2)HALFBIAS=0x1		0.8		V/μs
		(OPA2)BIASPROG=0x0, (OPA2)HALFBIAS=0x1		0.1		V/μs
N _{OPAMP}	Voltage Noise	V _{out} =1V, RESSEL=0, 0.1 Hz<f<10 kHz, OPAx- HCMDIS=0		101		μV _{RMS}
		V _{out} =1V, RESSEL=0, 0.1 Hz<f<10 kHz, OPAx- HCMDIS=1		141		μV _{RMS}

BGA112 Pin# and Name		Pin Alternate Functionality / Description				
Pin #	Pin Name	Analog	EBI	Timers	Communication	Other
A4	PE9		EBI_AD01 #0/1/2	PCNT2_S1IN #1		
A5	PD10		EBI_CS1 #0/1/2			
A6	PF7		EBI_BL1 #0/1/2	TIM0_CC1 #2	U0_RX #0	
A7	PF5		EBI_REn #0/2	TIM0_CDTI2 #2/5		PRS_CH2 #1
A8	PF4		EBI_WEn #0/2	TIM0_CDTI1 #2/5		PRS_CH1 #1
A9	PE4		EBI_A11 #0/1/2		US0_CS #1	
A10	PC14	ACMP1_CH6 DAC0_OUT1ALT #2/ OPAMP_OUT1ALT		TIM0_CDTI1 #1/3 TIM1_CC1 #0 PCNT0_S1IN #0	US0_CS #3 U0_TX #3	LES_CH14 #0
A11	PC15	ACMP1_CH7 DAC0_OUT1ALT #3/ OPAMP_OUT1ALT		TIM0_CDTI2 #1/3 TIM1_CC2 #0	US0_CLK #3 U0_RX #3	LES_CH15 #0 DBG_SWO #1
B1	PA15		EBI_AD08 #0/1/2	TIM3_CC2 #0		
B2	PE13		EBI_AD05 #0/1/2		US0_TX #3 US0_CS #0 I2C0_SCL #6	LES_ALTEX7 #0 ACMP0_O #0 GPIO_EM4WU5
B3	PE11		EBI_AD03 #0/1/2	TIM1_CC1 #1	US0_RX #0	LES_ALTEX5 #0 BOOT_RX
B4	PE8		EBI_AD00 #0/1/2	PCNT2_S0IN #1		PRS_CH3 #1
B5	PD11		EBI_CS2 #0/1/2			
B6	PF8		EBI_WEn #1	TIM0_CC2 #2		ETM_TCLK #1
B7	PF6		EBI_BL0 #0/1/2	TIM0_CC0 #2	U0_TX #0	
B8	PF3		EBI_ALE #0	TIM0_CDTI0 #2/5		PRS_CH0 #1 ETM_TD3 #1
B9	PE5		EBI_A12 #0/1/2		US0_CLK #1	
B10	PC12	ACMP1_CH4 DAC0_OUT1ALT #0/ OPAMP_OUT1ALT			U1_TX #0	CMU_CLK0 #1 LES_CH12 #0
B11	PC13	ACMP1_CH5 DAC0_OUT1ALT #1/ OPAMP_OUT1ALT		TIM0_CDTI0 #1/3 TIM1_CC0 #0 TIM1_CC2 #4 PCNT0_S0IN #0	U1_RX #0	LES_CH13 #0
C1	PA1		EBI_AD10 #0/1/2	TIM0_CC1 #0/1	I2C0_SCL #0	CMU_CLK1 #0 PRS_CH1 #0
C2	PA0		EBI_AD09 #0/1/2	TIM0_CC0 #0/1/4	I2C0_SDA #0 LEU0_RX #4	PRS_CH0 #0 GPIO_EM4WU0
C3	PE10		EBI_AD02 #0/1/2	TIM1_CC0 #1	US0_TX #0	BOOT_TX
C4	PD13					ETM_TD1 #1
C5	PD12		EBI_CS3 #0/1/2			
C6	PF9		EBI_REn #1			ETM_TD0 #1
C7	VSS	Ground.				
C8	PF2		EBI_ARDY #0/1/2	TIM0_CC2 #5	LEU0_TX #4	ACMP1_O #0 DBG_SWO #0 GPIO_EM4WU4
C9	PE6		EBI_A13 #0/1/2		US0_RX #1	
C10	PC10	ACMP1_CH2	EBI_A10 #1/2	TIM2_CC2 #2	US0_RX #2	LES_CH10 #0
C11	PC11	ACMP1_CH3	EBI_ALE #1/2		US0_TX #2	LES_CH11 #0
D1	PA3		EBI_AD12 #0/1/2	TIM0_CDTI0 #0	U0_TX #2	LES_ALTEX2 #0

Alternate	LOCATION							
Functionality	0	1	2	3	4	5	6	Description
ACMP0_CH4	PC4							Analog comparator ACMP0, channel 4.
ACMP0_CH5	PC5							Analog comparator ACMP0, channel 5.
ACMP0_CH6	PC6							Analog comparator ACMP0, channel 6.
ACMP0_CH7	PC7							Analog comparator ACMP0, channel 7.
ACMP0_O	PE13	PE2	PD6					Analog comparator ACMP0, digital output.
ACMP1_CH0	PC8							Analog comparator ACMP1, channel 0.
ACMP1_CH1	PC9							Analog comparator ACMP1, channel 1.
ACMP1_CH2	PC10							Analog comparator ACMP1, channel 2.
ACMP1_CH3	PC11							Analog comparator ACMP1, channel 3.
ACMP1_CH4	PC12							Analog comparator ACMP1, channel 4.
ACMP1_CH5	PC13							Analog comparator ACMP1, channel 5.
ACMP1_CH6	PC14							Analog comparator ACMP1, channel 6.
ACMP1_CH7	PC15							Analog comparator ACMP1, channel 7.
ACMP1_O	PF2	PE3	PD7					Analog comparator ACMP1, digital output.
ADC0_CH0	PD0							Analog to digital converter ADC0, input channel number 0.
ADC0_CH1	PD1							Analog to digital converter ADC0, input channel number 1.
ADC0_CH2	PD2							Analog to digital converter ADC0, input channel number 2.
ADC0_CH3	PD3							Analog to digital converter ADC0, input channel number 3.
ADC0_CH4	PD4							Analog to digital converter ADC0, input channel number 4.
ADC0_CH5	PD5							Analog to digital converter ADC0, input channel number 5.
ADC0_CH6	PD6							Analog to digital converter ADC0, input channel number 6.
ADC0_CH7	PD7							Analog to digital converter ADC0, input channel number 7.
BOOT_RX	PE11							Bootloader RX.
BOOT_TX	PE10							Bootloader TX.
BU_STAT	PE3							Backup Power Domain status, whether or not the system is in backup mode
BU_VIN	PD8							Battery input for Backup Power Domain
BU_VOUT	PE2							Power output for Backup Power Domain
CMU_CLK0	PA2	PC12	PD7					Clock Management Unit, clock output number 0.
CMU_CLK1	PA1	PD8	PE12					Clock Management Unit, clock output number 1.
OPAMP_N0	PC5							Operational Amplifier 0 external negative input.
OPAMP_N1	PD7							Operational Amplifier 1 external negative input.
OPAMP_N2	PD3							Operational Amplifier 2 external negative input.
DAC0_OUT0 / OPAMP_OUT0	PB11							Digital to Analog Converter DAC0_OUT0 / OPAMP output channel number 0.
DAC0_OUT0ALT / OPAMP_OUT0ALT	PC0	PC1	PC2	PC3	PD0			Digital to Analog Converter DAC0_OUT0ALT / OPAMP alternative output for channel 0.
DAC0_OUT1 / OPAMP_OUT1	PB12							Digital to Analog Converter DAC0_OUT1 / OPAMP output channel number 1.
DAC0_OUT1ALT / OPAMP_OUT1ALT	PC12	PC13	PC14	PC15	PD1			Digital to Analog Converter DAC0_OUT1ALT / OPAMP alternative output for channel 1.
OPAMP_OUT2	PD5	PD0						Operational Amplifier 2 output.
OPAMP_P0	PC4							Operational Amplifier 0 external positive input.
OPAMP_P1	PD6							Operational Amplifier 1 external positive input.

7 Revision History

7.1 Revision 1.40

March 21st, 2016

Added clarification on conditions for INL_{ADC} and DNL_{ADC} parameters.

Reduced maximum and typical current consumption for all EM0 entries except 48 MHz in the Current Consumption table in the Electrical Characteristics section.

Increased maximum specifications for EM2 current, EM3 current, and EM4 current in the Current Consumption table in the Electrical Characteristics section.

Increased typical specification for EM2 and EM3 current at 85 C in the Current Consumption table in the Electrical Characteristics section.

Added EM2, EM3, and EM4 current consumption vs. temperature graphs.

Added a new EM2 entry and specified the existing specification is for EM0 for the BOD threshold on falling external supply voltage in the Power Management table in the Electrical Characteristics section.

Reduced maximum input leakage current in the GPIO table in the Electrical Characteristics section.

Added a maximum current consumption specification to the LFRCO table in the Electrical Characteristics section.

Added maximum specifications for the active current including references for two channels to the DAC table in the Electrical Characteristics section.

Increased the maximum specification for DAC offset voltage in the DAC table in the Electrical Characteristics section.

Increased the typical specifications for active current with $FULLBIAS=1$ and capacitive sense internal resistance in the ACMP table in the Electrical Characteristics section.

Added minimum and maximum specifications and updated the typical value for the VCMP offset voltage in the VCMP table in the Electrical Characteristics section.

Removed the maximum specification and reduced the typical value for hysteresis in the VCMP table in the Electrical Characteristics section.

Updated all graphs in the Electrical Characteristics section to display data for 2.0 V as the minimum voltage.

7.2 Revision 1.30

May 23rd, 2014

Removed "preliminary" markings

Updated HFRCO figures.

Corrected single power supply voltage minimum value from 1.85V to 1.98V.

Updated Current Consumption information.

Updated Power Management information.

7.10 Revision 0.91

March 21th, 2011

Added new alternative locations for EBI and SWO.

Corrected slew rate data for Opamps.

7.11 Revision 0.90

February 4th, 2011

Initial preliminary release.

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